

AMENDMENTS TO THE SPECIFICATION

1. Please substitute the paragraph [0009] on page 4 with the following amended paragraph:

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It is therefore a primary objective of the claimed invention to provide a method of fabricating a polysilicon film by an excimer laser crystallization process which comprises a step of forming a heat-retaining capping layer so as to increase the grain size of the polysilicon film and improve the performance of devices.

10 2. Please substitute the paragraph [0010] on page 4 with the following amended paragraph:

15 In a preferred embodiment, the claimed invention provides a method of fabricating a polysilicon film by an excimer laser crystallization process. First, a substrate comprising a first region and a second region is provided. An amorphous silicon layer and a mask layer are formed on the substrate in sequence. Then, a photo-etching process is performed to remove the mask layer in the first region. A heat-retaining 20 capping layer is formed on the mask layer and the amorphous silicon layer. After that, an excimer laser 25 crystallization process is performed so that the amorphous silicon layer in the first region is crystallized into a polysilicon film.

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